

Features

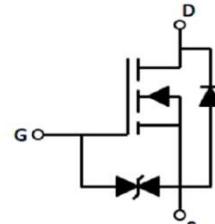
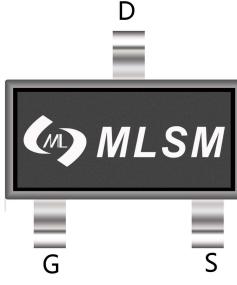
- Low On-Resistance
- Low Threshold
- Fast Switching Speed
- ESD protected up to 2KV

Application

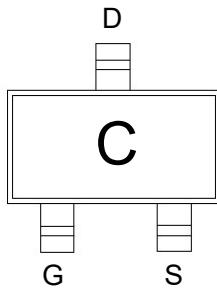
- Battery Operated Systems
- Power Supply Converter Circuits
- Load/Power Switching Cell Phones, Pagers

Product Summary

V_{DS}	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
20V	700m Ω @4.5V	0.5A
	850m Ω @2.5V	



Schematic diagram



C: Device code

Marking and pin assignment



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
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Common Ratings (TC=25°C Unless Otherwise Noted)

V_{DS}	Drain-Source Breakdown Voltage	20	V
V_{GS}	Gate-Source Voltage	± 12	V
T_J	Maximum Junction Temperature	150	°C
T_{STG}	Storage Temperature Range	-50 to 155	°C
I_S	Diode Continuous Forward Current	Tc=25°C 0.5	A

Mounted on Large Heat Sink

I_{DM}	Pulse Drain Current Tested	Tc=25°C 3	A
I_D	Continuous Drain Current	Tc=25°C 0.5	A
P_D	Maximum Power Dissipation	Tc=25°C 0.15	W
E_{SD}	Gate-Source ESD Rating (HBM, Method 3015)	2000	V

Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MLS1012KT	SOT-523	C	3,000	45,000	180,000	7" reel

Electrical Characteristics (TJ=25°C unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
$BV_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	20	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=20V, V_{GS}=0V$	--	--	1	μA
I_{GSS}	Gate-Body Leakage Current	$V_{GS}=\pm 10V, V_{DS}=0V$	--	--	± 20	μA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	0.45	0.7	1.2	V
$R_{DS(on)}$	Drain-Source On-State Resistance	$V_{GS}=4.5V, I_D=0.6A$	--	250	700	$m\Omega$
		$V_{GS}=2.5V, I_D=0.5A$	--	330	850	$m\Omega$

Dynamic Electrical Characteristics @ TJ = 25°C (unless otherwise stated)

C_{ISS}	Input Capacitance	$V_{DS}=10V, V_{GS}=0V, f=1MHz$	--	33	--	pF
C_{OSS}	Output Capacitance		--	21	--	pF
C_{RSS}	Reverse Transfer Capacitance		--	10	--	pF

Switching Characteristics

Q_g	Total Gate Charge	$V_{DS}=10V, I_D=0.5A, V_{GS}=4.5V$	--	0.8	--	nC
Q_{gs}	Gate Source Charge		--	0.3	--	nC
Q_{gd}	Gate Drain Charge		--	0.17	--	nC
$t_{d(on)}$	Turn-on Delay Time	$V_{DD}=10V, I_D=0.5A, V_{GS}=4.5V, R_G=10\Omega$	--	4.2	--	nS
t_r	Turn-on Rise Time		--	19.1	--	nS
$t_{d(off)}$	Turn-Off Delay Time		--	10.3	--	nS
t_f	Turn-Off Fall Time		--	24	--	nS

Source- Drain Diode Characteristics

V_{SD}	Forward on voltage	$T_j=25^\circ C, I_S=0.5A$	--	--	1.2	V
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Typical Operating Characteristics

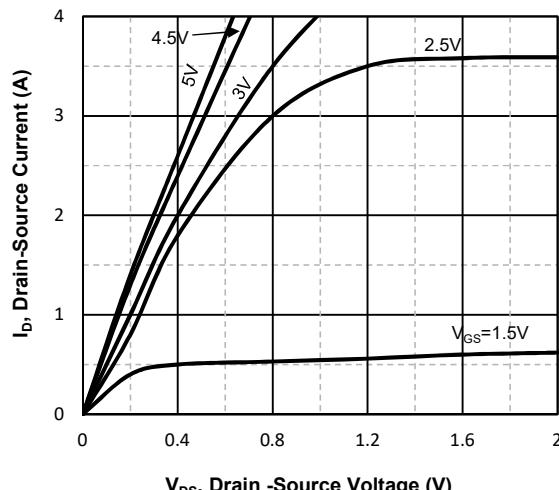


Fig1. Typical Output Characteristics

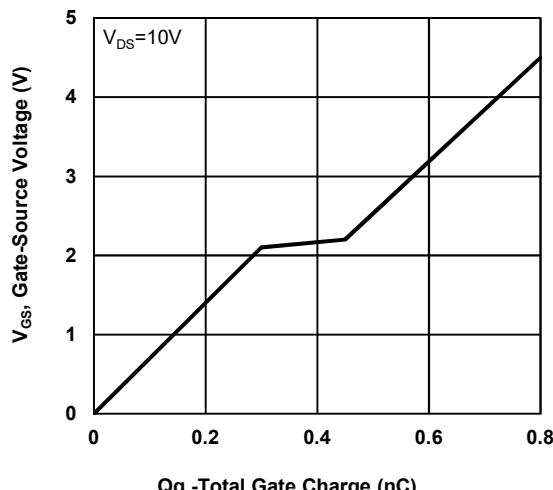


Fig2. Typical Gate Charge Vs.Gate-Source Voltage

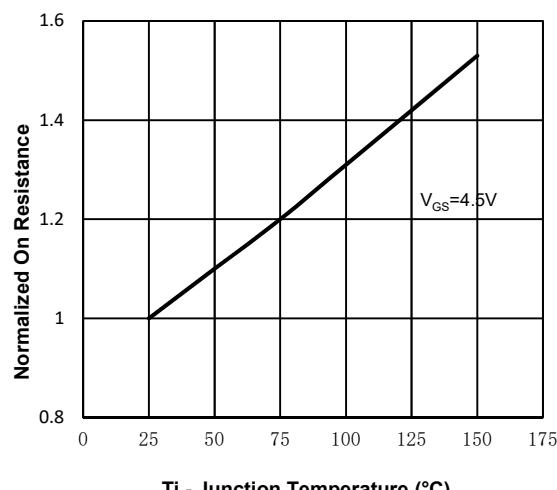


Fig3. Normalized On-Resistance Vs. Temperature

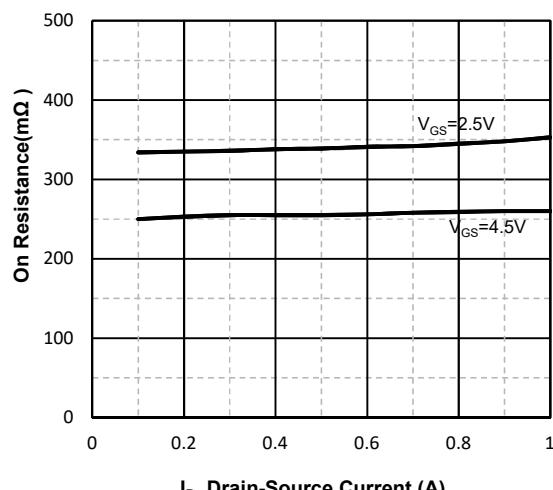


Fig4. On-Resistance Vs. Drain-Source Current

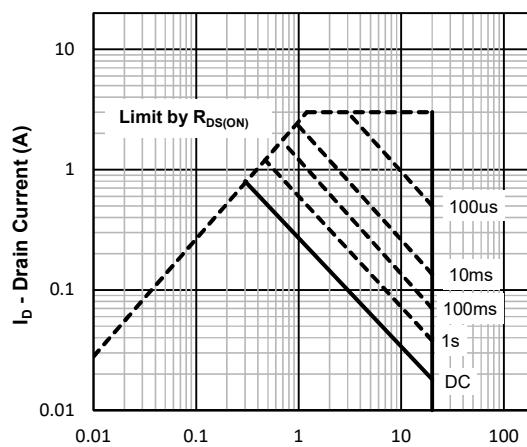


Fig5. Maximum Safe Operating Area

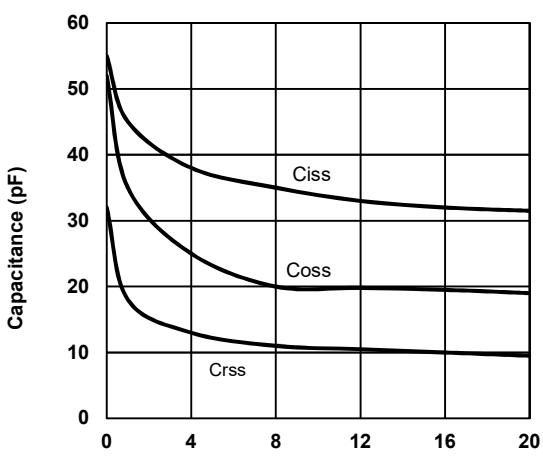
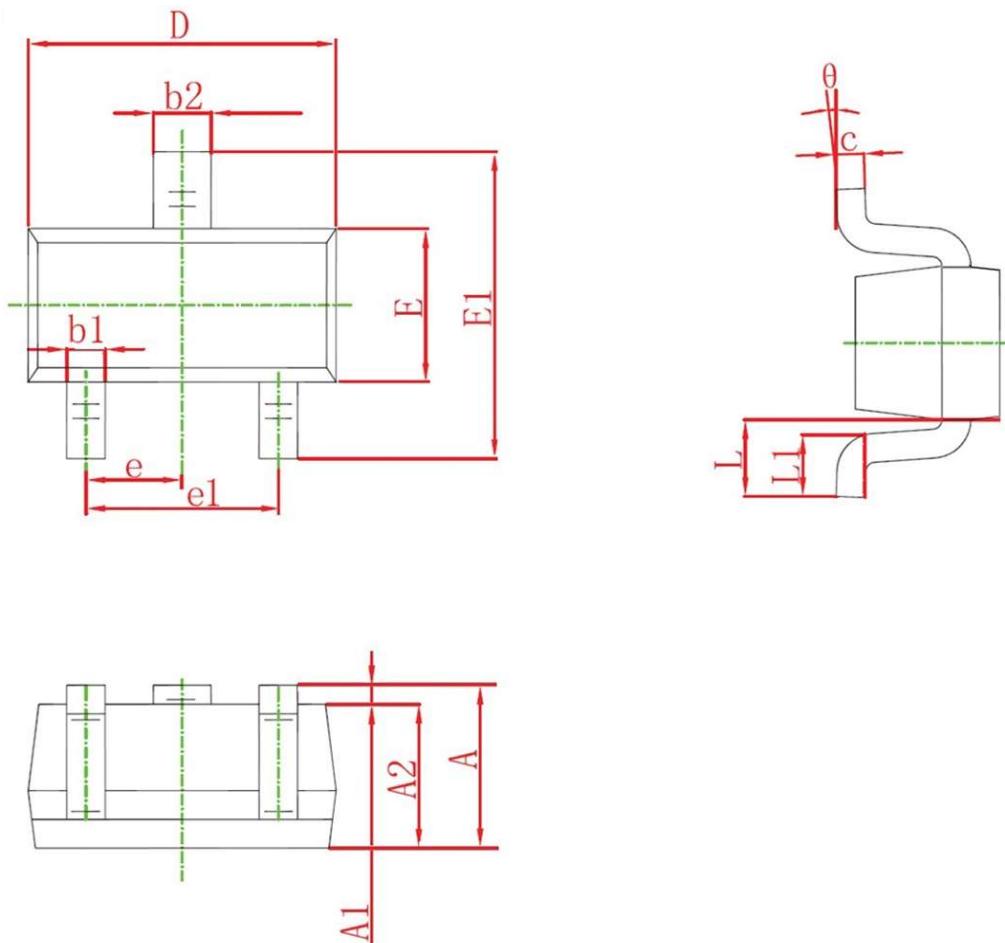


Fig6 Typical Capacitance Vs.Drain-Source Voltage

SOT-523 Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500TYP		0.020TYP	
e1	0.900	1.100	0.035	0.043
L	0.400REF		0.016REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°